



### **40V N-Channel Enhancement Mode MOSFET**

Voltage

40 V

Current

70A

#### **Features**

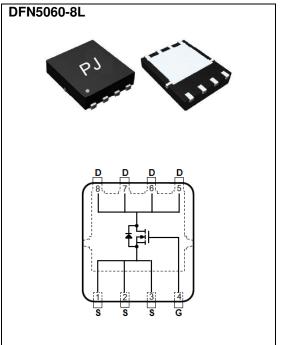
- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@20A<6.5m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}$ @4.5V,  $I_{D}$ @10A<9m $\Omega$
- High switching speed
- Improved dv/dt capability
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams



### **Maximum Ratings and Thermal Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	40	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20		
Continuous Drain Current (Note 4)	T <sub>C</sub> =25°C	I <sub>D</sub>	70	А	
	T <sub>C</sub> =100°C		44		
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	280		
Power Dissipation	T <sub>C</sub> =25°C	Po	100	14/	
	T <sub>C</sub> =100°C		50	W	
Continuous Drain Current (Note 4)	T <sub>A</sub> =25°C	Ι <sub>D</sub>	12.7		
	T <sub>A</sub> =70°C		10	Α	
Power Dissipation	T <sub>A</sub> =25°C	Po	2.4	147	
	T <sub>A</sub> =70°C		1.6	W	
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	80	mJ	
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~175	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	1.5	°C/W	
	Junction to Ambient	$R_{ heta JA}$	62.5		

• Limited only By Maximum Junction Temperature





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}$ =0V, $I_D$ =250uA	40	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1	1.61	2.5		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =10V, $I_D$ =20A	-	5.5	6.5	mΩ	
		$V_{GS}$ =4.5V, $I_{D}$ =10A	-	7	9		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =40V, $V_{GS}$ =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	$Q_g$	V <sub>DS</sub> =20V, I <sub>D</sub> =10A, V <sub>GS</sub> =4.5V (Note 1,2)	-	17	-	nC	
Gate-Source Charge	$Q_gs$		-	4.9	-		
Gate-Drain Charge	$Q_{gd}$		-	6.4	-		
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHZ	-	1759	-	pF	
Output Capacitance	Coss		-	176	-		
Reverse Transfer Capacitance	Crss	I=IIVIITZ	-	126	-		
Turn-On Delay Time	td <sub>(on)</sub>	\/ 45\/   4 A	-	11	-		
Turn-On Rise Time	t <sub>r</sub>	$V_{DD}$ =15V, $I_{D}$ =1A, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	21	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>		-	40	-		
Turn-Off Fall Time	t <sub>f</sub>		-	25	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	ı				70	Α	
Diode Forward Current	I <sub>S</sub>		-	-	70	^	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.7	1	V	

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =40A,  $V_{DD}$ =25V,  $V_{GS}$ =10V.
- 7. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

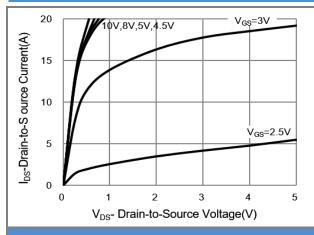
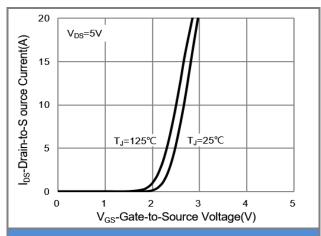


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

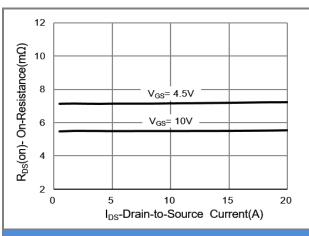


Fig.3 On-Resistance vs. Drain Current

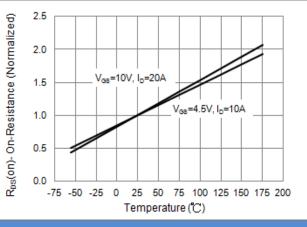


Fig.4 On-Resistance vs. Junction temperature

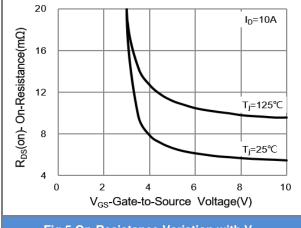


Fig.5 On-Resistance Variation with V<sub>GS</sub>

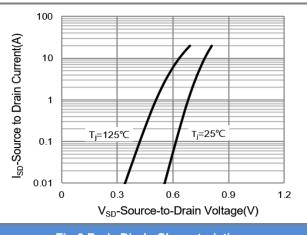


Fig.6 Body Diode Characteristics





#### **TYPICAL CHARACTERISTIC CURVES**

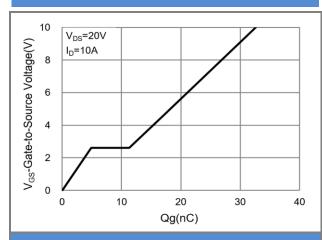


Fig.7 Gate-Charge Characteristics

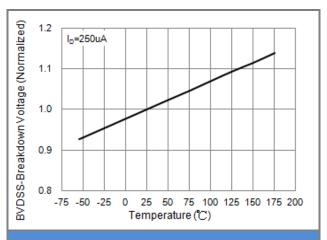


Fig.8 Breakdown Voltage Variation vs. Temperature

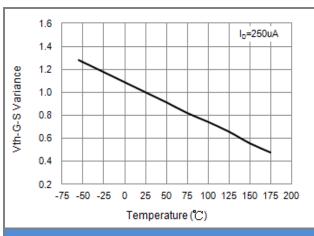


Fig.9 Threshold Voltage Variation with Temperature

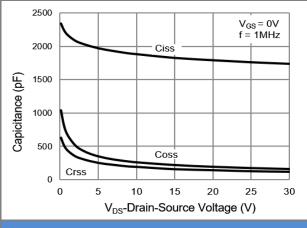


Fig.10 Capacitance vs. Drain-Source Voltage

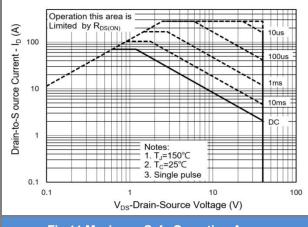


Fig.11 Maximum Safe Operating Area

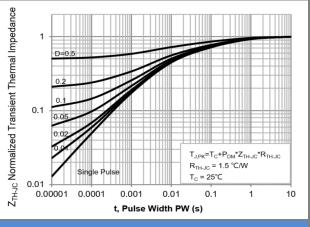


Fig.12 Normalized Transient Thermal Impedance

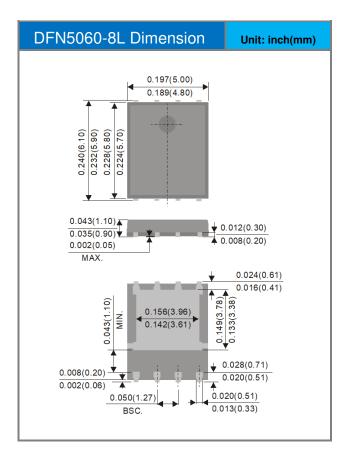


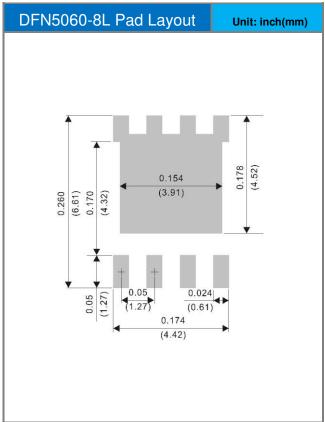


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5444-AU_R2_000A1	DFN5060-8L	3000pcs / 13" reel	Q5444	Halogen free	

### **Packaging Information & Mounting Pad Layout**









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